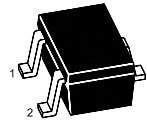


MMBTSD2652W

NPN Silicon Epitaxial Planar Transistor

for low frequency amplifier and general purpose amplification application



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

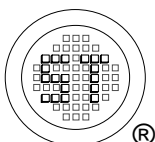
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	15	V
Collector Emitter Voltage	V_{CEO}	12	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C $I_{CP}^{1)}$	1.5 3	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

¹⁾ Single pulse, $P_w = 1\text{ ms}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 200\text{ mA}$	h_{FE}	270	-	680	-
Collector Cutoff Current at $V_{CB} = 15\text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	15	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	12	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 25\text{ mA}$	$V_{CE(sat)}$	-	-	0.2	V
Transition Frequency at $V_{CE} = 2\text{ V}$, $-I_E = 200\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	400	-	MHz
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	12	-	pF

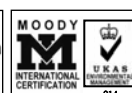


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(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
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Certificate No. 7116



ISO 9001:2000
Certificate No. 0506088

Dated : 15/05/2007

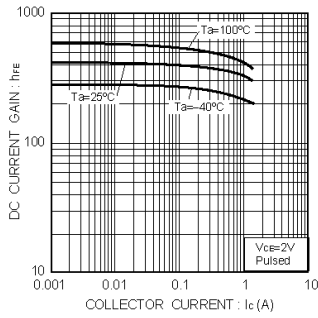


Fig.1 DC current gain vs. collector current

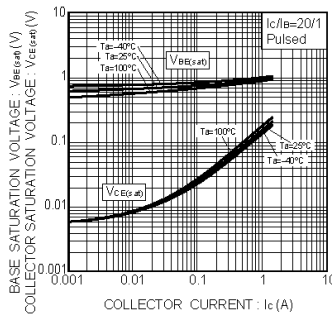


Fig.2 Collector-emitter saturation voltage vs. collector current

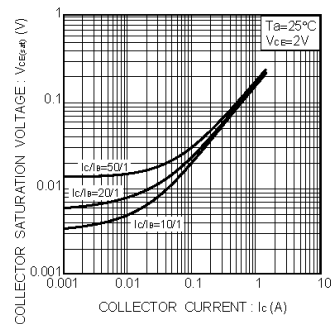


Fig.3 Collector-emitter saturation voltage vs. collector current

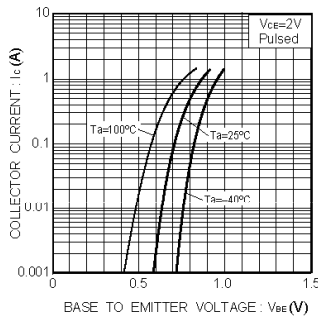


Fig.4 Grounded emitter propagation characteristics

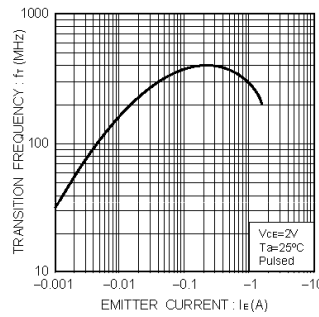


Fig.5 Gain bandwidth product vs. emitter current

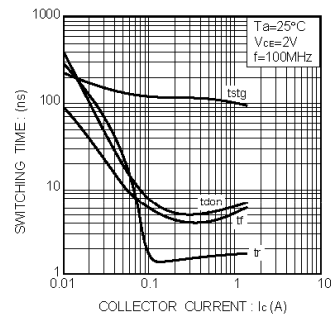


Fig.6 Switching time

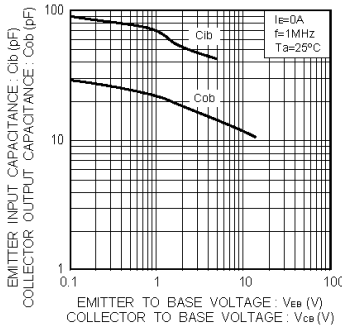


Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

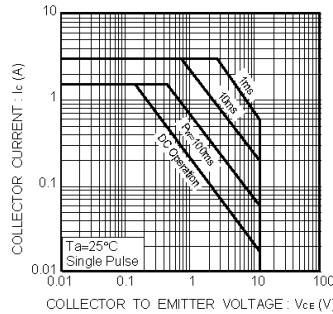
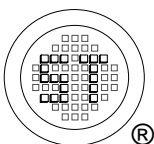


Fig.8 Safe Operating Area



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